

60 V, N-channel Trench MOSFET 21 March 2016

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

#### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	3.1	А
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C		-	46	60	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

## 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMV55ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV55ENEA	DL%

[1] % = placeholder for manufacturing site code

#### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

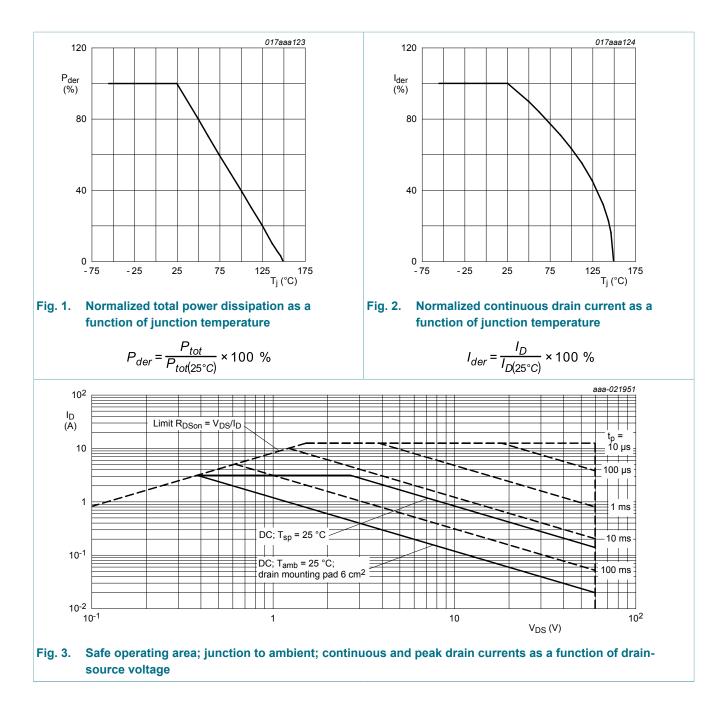
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage	-		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	3.1	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	2	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	12.6	А
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I <sub>D</sub> = 0.56 A; DUT in avalanche (unclamped)		-	17	mJ
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	478	mW
			[1]	-	1.19	W
		T <sub>sp</sub> = 25 °C		-	8.36	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode					,
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.3	А
ESD maxim	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V
	I					

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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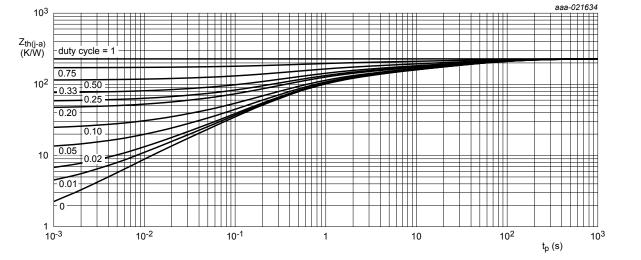


#### 9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ung a)	thermal resistance from junction to ambient	in free air	[1]	-	227	262	K/W
			[2]	-	91	105	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	13	15	K/W

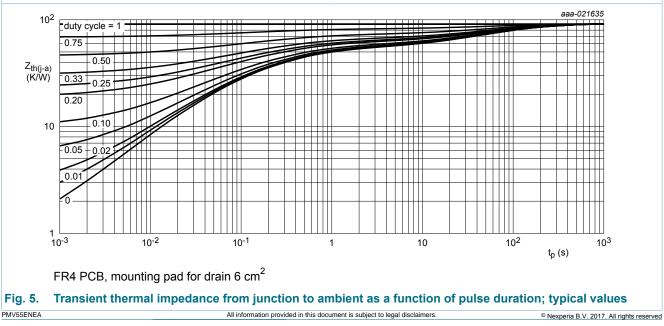
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint





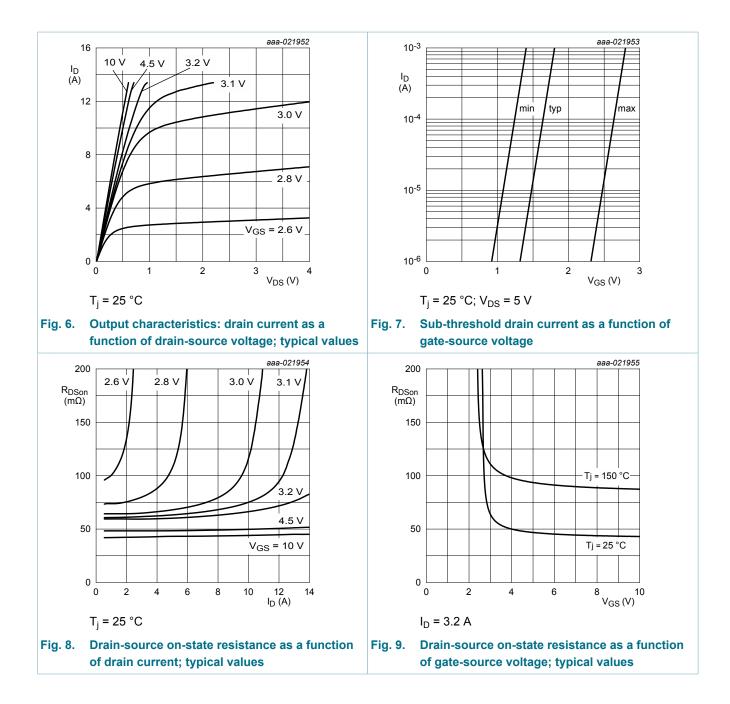
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	10	μA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μA
		$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C	-	46	60	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 150 °C	-	92	120	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 2.9 A; T <sub>j</sub> = 25 °C	-	52	70	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C	-	18.2	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	8	-	Ω
Dynamic ch	aracteristics	1				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 30 V; I <sub>D</sub> = 3.1 A; V <sub>GS</sub> = 10 V;	-	12.7	19	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.3	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.4	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 30 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	646	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	49	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	36	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; I <sub>D</sub> = 3.1 A; V <sub>GS</sub> = 10 V;	-	9	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	13	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	33	-	ns
t <sub>f</sub>	fall time		-	13	-	ns
Source-drai	n diode	1	ı I			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.3 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.8	1.2	V

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## **PMV55ENEA**

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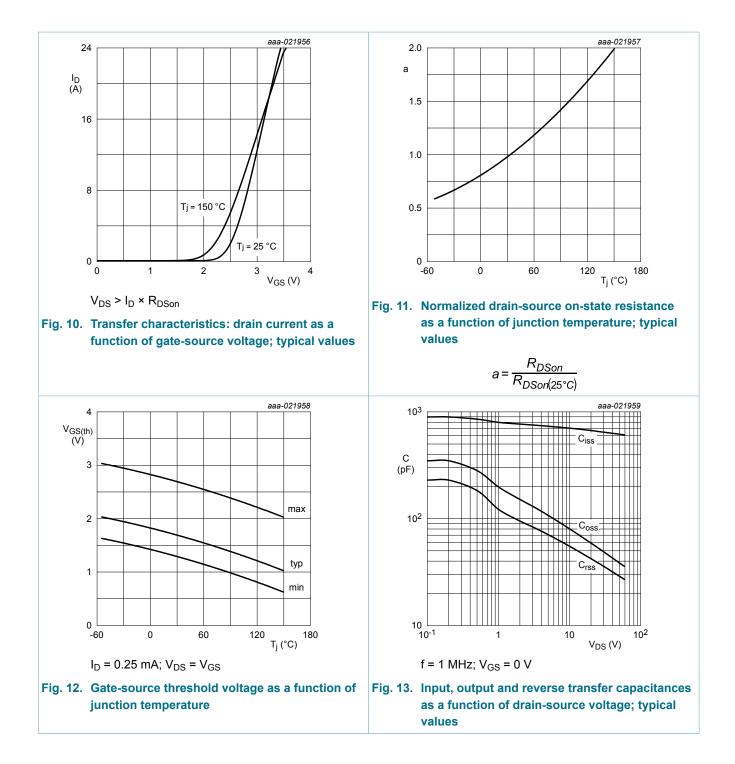


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## **PMV55ENEA**

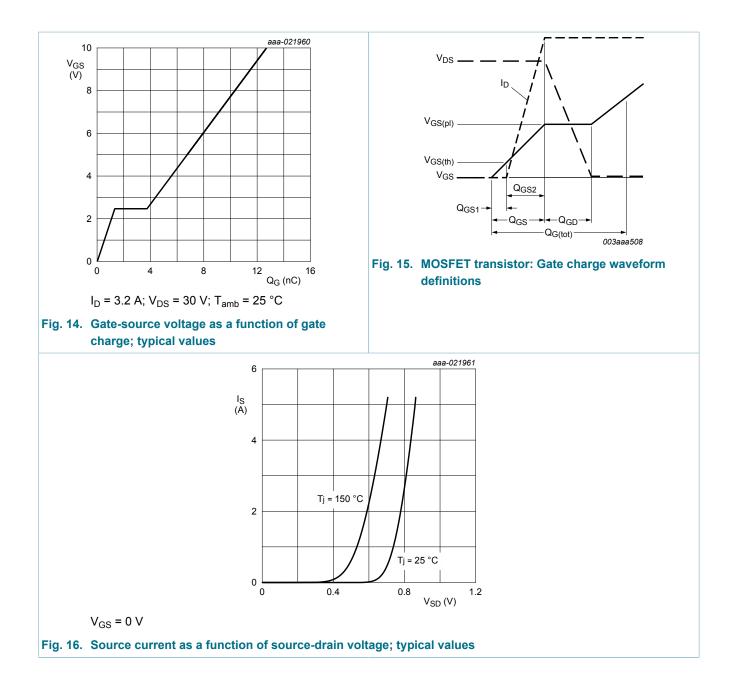
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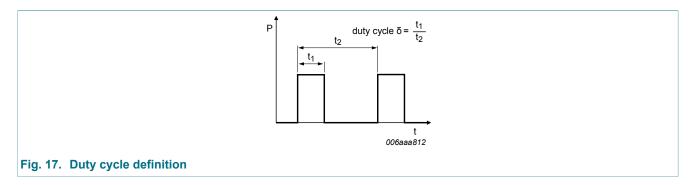
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## **PMV55ENEA**

#### 60 V, N-channel Trench MOSFET



## **11. Test information**

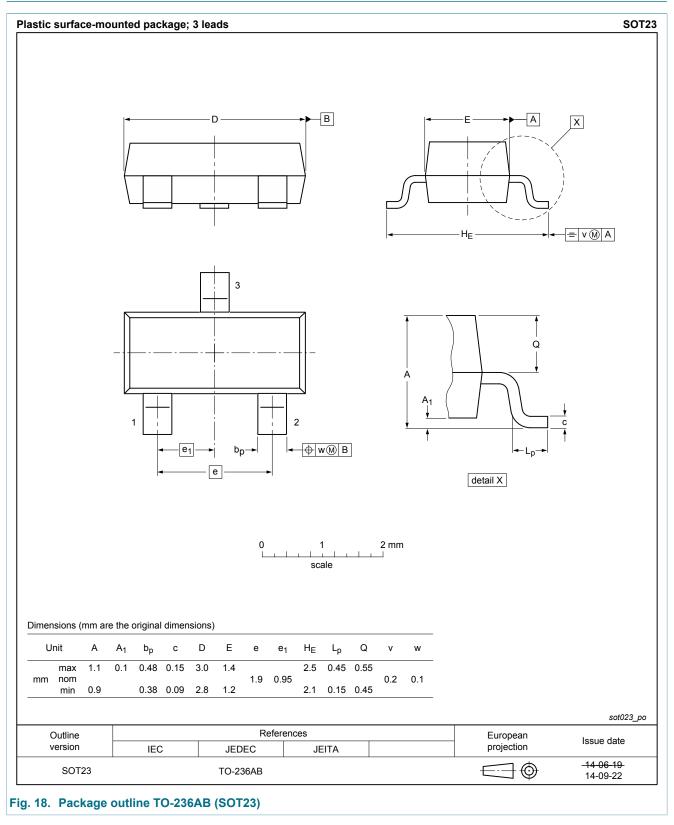


#### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

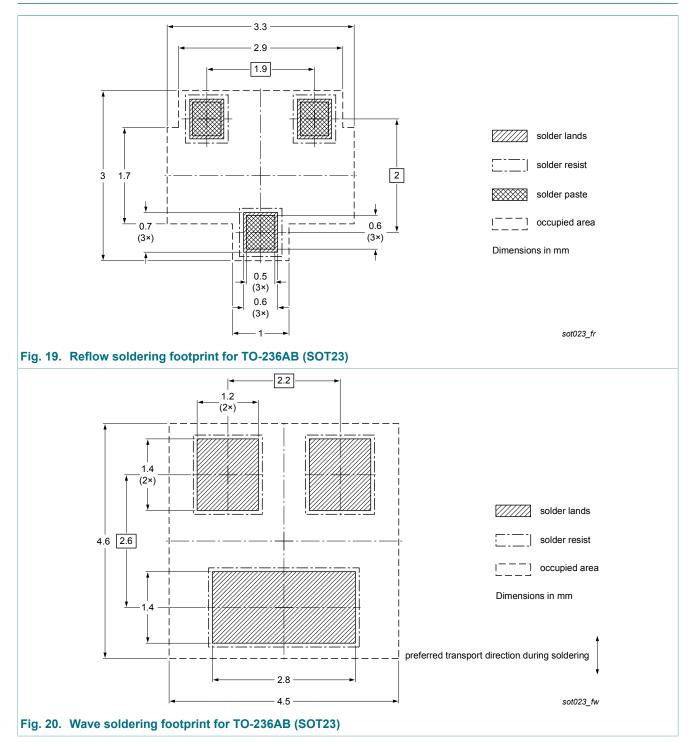
#### 60 V, N-channel Trench MOSFET

## 12. Package outline



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## 13. Soldering



## 14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMV55ENEA v.1	20160321	Product data sheet	-	-			

#### 60 V, N-channel Trench MOSFET

#### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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	General description

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